
HM621664H/HM621864H Series

65536-word × 16/18-bit High Speed CMOS Static RAM

HITACHI

Description

The HM621664H/HM621864H is an asynchronous high speed static RAM organized as 64-kword × 16/18-bit. It realize high speed access time (20/25 ns) with employing 0.8 μm CMOS process and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The HM621664H/HM621864H is packaged in 400-mil 44-pin SOJ for high density surface mounting.

Features

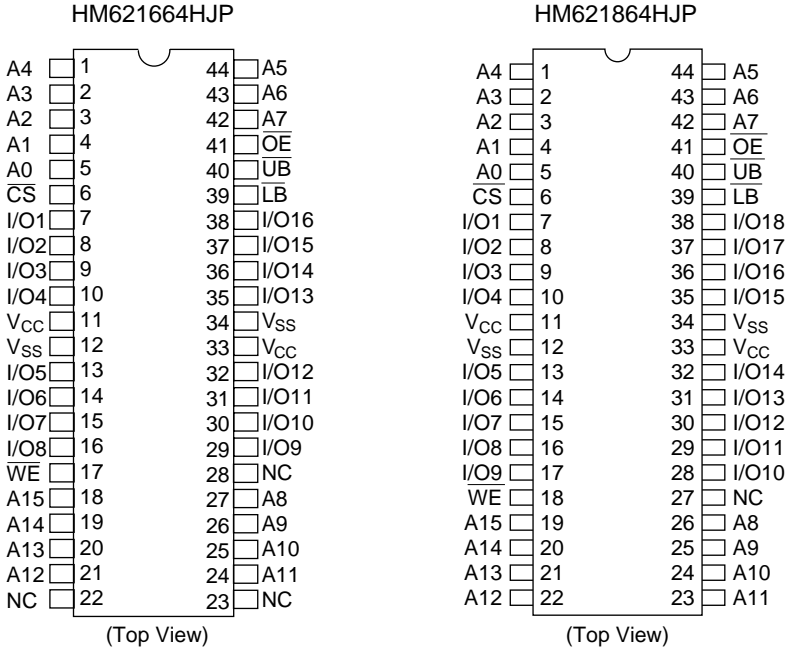
- Single 5 V supply: 5 V ± 10%
- Access time 20/25 ns (max)
- Completely static memory
 - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
 - All inputs and outputs
- 400-mil 44-pin SOJ package
- Center V_{CC} and V_{SS} type pinout

Ordering Information

Type No.	Access Time	Package
HM621664HJP-20	20 ns	400-mil 44-pin plastic SOJ (CP-44D)
HM621664HJP-25	25 ns	
HM621664HLJP-20	20 ns	
HM621664HLJP-25	25 ns	
HM621864HJP-20	20 ns	
HM621864HJP-25	25 ns	
HM621864HLJP-20	20 ns	
HM621864HLJP-25	25 ns	

HM621664H/HM621864H Series

Pin Arrangement

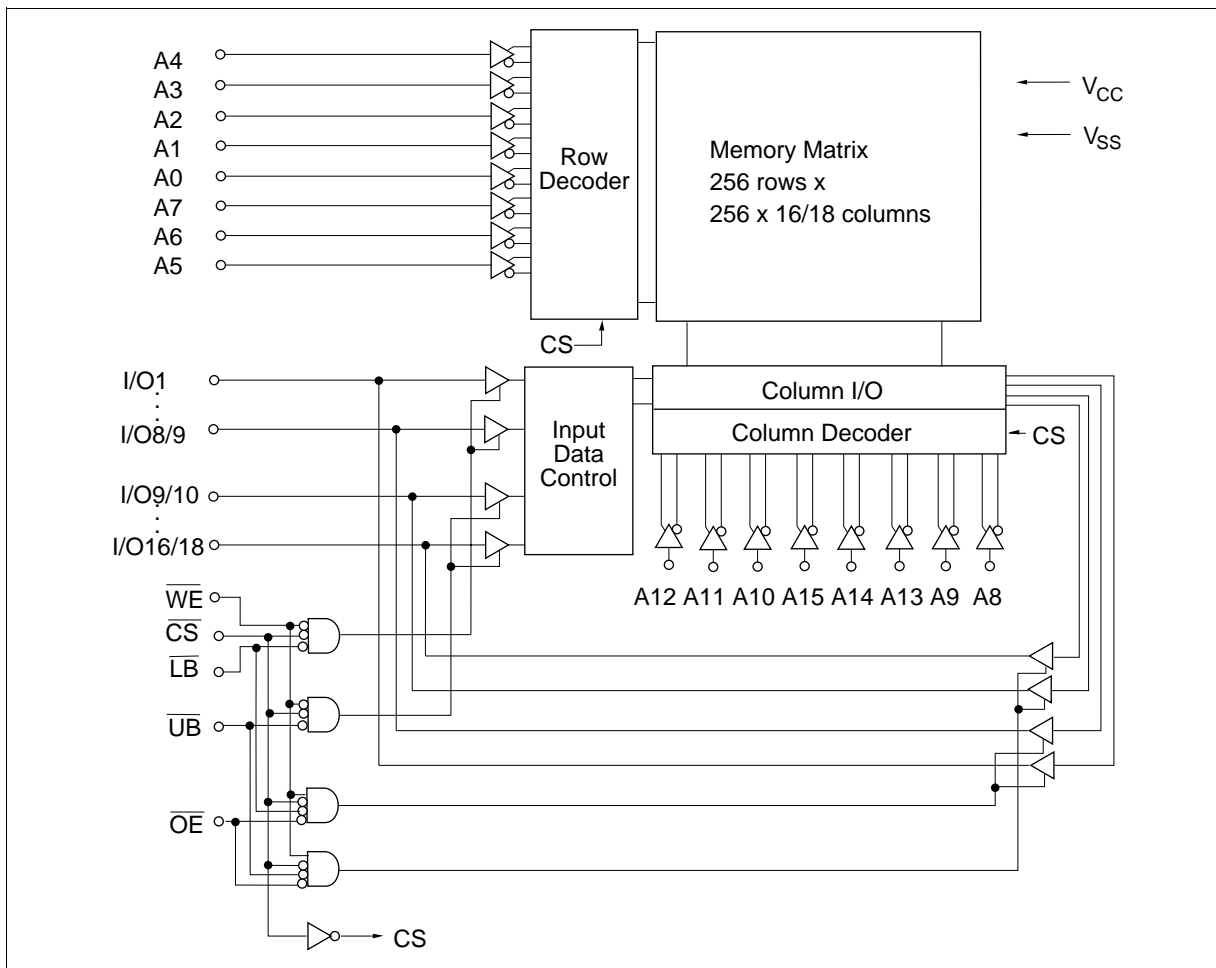


Pin Description

Pin Name

HM621664H	HM621864H	Function
A0 – A15	A0 – A15	Address
I/O1 – I/O8	I/O1 – I/O9	Input/output (lower byte)
I/O9 – I/O16	I/O10 – I/O18	Input/output (upper byte)
CS	CS	Chip select
LB	LB	Lower byte select
UB	UB	Upper byte select
WE	WE	Write enable
OE	OE	Output enable
V _{CC}	V _{CC}	Power supply
V _{SS}	V _{SS}	Ground
NC	NC	No connection

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	-0.5 to +7.0	V
Voltage on any pin relative to V_{SS}	V_T	-0.5 ¹ to $V_{CC} + 0.5$	V
Power dissipation	P_T	$1.0^{2} / 1.5^{3}$	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C
Storage temperature under bias	T_{bias}	-10 to +85	°C

- Notes: 1. -2.5 V for pulse width (under shoot) ≤ 10 ns
 2. at still air condition
 3. at air flow ≥ 1.0 m/s

HM621664H/HM621864H Series

Function Table

\overline{CS}	\overline{OE}	\overline{WE}	\overline{LB}	\overline{UB}	V_{CC} Current	I/O (Lower Byte)	I/O (Upper Byte)	Ref. Cycle
H	X	X	X	X	I_{SB}, I_{SB1}	High-Z	High-Z	—
L	H	H	X	X	I_{CC}	High-Z	High-Z	—
L	L	H	L	L	I_{CC}	Output	Output	Read cycle
L	L	H	L	H	I_{CC}	Output	High-Z	Read cycle
L	L	H	H	L	I_{CC}	High-Z	Output	Read cycle
L	L	H	H	H	I_{CC}	High-Z	High-Z	—
L	X	L	L	L	I_{CC}	Input	Input	Write cycle
L	X	L	L	H	I_{CC}	Input	High-Z	Write cycle
L	X	L	H	L	I_{CC}	High-Z	Input	Write cycle
L	X	L	H	H	I_{CC}	High-Z	High-Z	—

Note: X: H or L

Recommended DC Operating Conditions ($T_a = 0$ to $+70^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage ²	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.2	—	$V_{CC} + 0.5$	V
	V_{IL}	-0.5^{*1}	—	0.8	V

Notes: 1. -2.0 V for pulse width (under shoot) ≤ 10 ns

2. The supply voltage with all V_{CC} pins must be on the same level.

The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Min	Typ ^{*1}	Max	Unit	Test Conditions	Note
Input leakage current	$ I_{LI} $	—	—	2	μA	$V_{in} = V_{SS}$ to V_{CC}	
Output leakage current	$ I_{LO} $	—	—	2	μA	$V_{IO} = V_{SS}$ to V_{CC}	
Operating power supply current	I_{CC}	—	160	220	mA	20 ns cycle	$\overline{CS} = V_{IL}$, $I_{out} = 0\text{ mA}$ Other inputs = V_{IH}/V_{IL}
			—	145	200	mA	
Standby power supply current	I_{SB}	—	50	90	mA	20 ns cycle	$\overline{CS} = V_{IH}$, Other inputs = V_{IH}/V_{IL}
			—	40	85	mA	
Standby power supply current (1)	I_{SB1}	—	—	2	mA	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2\text{ V}$, $0\text{ V} \leq V_{in} \leq 0.2\text{ V}$ or $V_{CC} \geq V_{in} \geq V_{CC} - 0.2\text{ V}$	
				—	—	0.2	mA
Output voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 8\text{ mA}$	
	V_{OH}	2.4	—	—	V	$I_{OH} = -4\text{ mA}$	

Note: 1. Typical values are at $V_{CC} = 5.0\text{ V}$, $T_a = +25^\circ\text{C}$ and not guaranteed.

Capacitance ($T_a = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)^{*1}

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance	C_{in}	—	—	6	pF	$V_{in} = 0\text{ V}$
Input/output capacitance	C_{IO}	—	—	8	pF	$V_{IO} = 0\text{ V}$

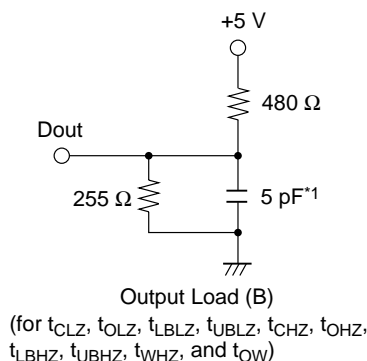
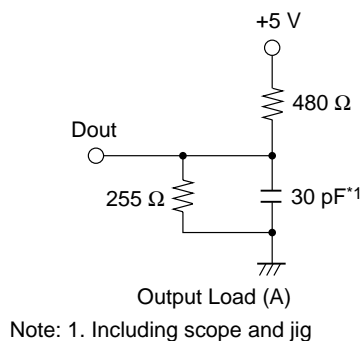
Note: 1. This parameter is sampled and not 100% tested.

HM621664H/HM621864H Series

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{SS} to 3.0 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures



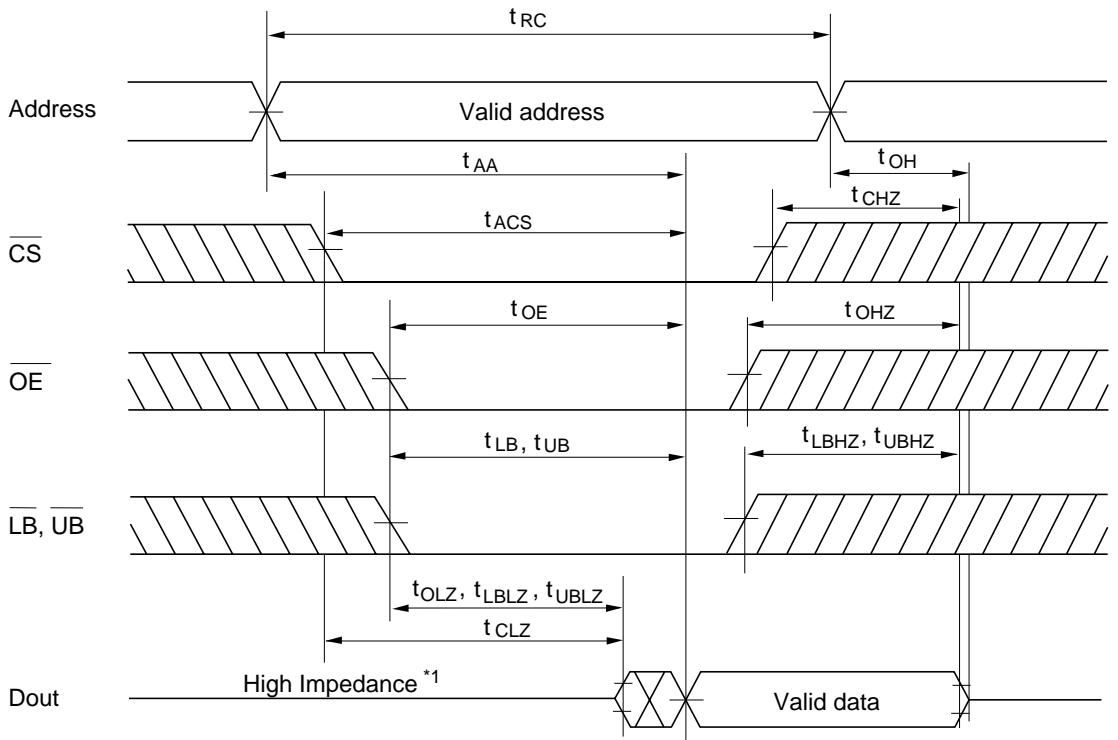
Read Cycle

HM621664H/HM621864H

Parameter	Symbol	-20		-25		Unit	Note
		Min	Max	Min	Max		
Read cycle time	t_{RC}	20	—	25	—	ns	
Address access time	t_{AA}	—	20	—	25	ns	
Chip select access time	t_{ACS}	—	20	—	25	ns	
Output enable to output valid	t_{OE}	—	10	—	12	ns	
Byte select to output valid	t_{LB} , t_{UB}	—	10	—	12	ns	
Output hold from address change	t_{OH}	5	—	5	—	ns	
Chip select to output in low-Z	t_{CLZ}	3	—	3	—	ns	1
Output enable to output in low-Z	t_{OLZ}	1	—	1	—	ns	1
Byte select to output in low-Z	t_{LBLZ} , t_{UBLZ}	1	—	1	—	ns	1
Chip deselect to output in high-Z	t_{CHZ}	—	7	—	7	ns	1
Output disable to output in high-Z	t_{OHZ}	—	7	—	7	ns	1
Byte deselect to output in high-Z	t_{LBHZ} , t_{UBHZ}	—	7	—	7	ns	1

Note: 1. Transition is measured ± 200 mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.

Read Timing Waveform ($\overline{WE} = V_{IH}$)



Note: 1. When \overline{CS} , \overline{OE} and \overline{LB} are low, Dout (lower byte) is low impedance.
 When \overline{CS} , \overline{OE} and \overline{UB} are low, Dout (upper byte) is low impedance.

HM621664H/HM621864H Series

Write Cycle

Parameter	Symbol	HM621664H/HM621864H				Unit	Notes
		-20		-25			
		Min	Max	Min	Max		
Write cycle time	t_{WC}	20	—	25	—	ns	
Address valid to end of write	t_{AW}	15	—	20	—	ns	
Chip select to end of write	t_{CW}	12	—	12	—	ns	
Write pulse width	t_{WP}	12	—	12	—	ns	
Byte select to end of write	t_{LBW}, t_{UBW}	12	—	12	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	2
Write recovery time	t_{WR}	0	—	0	—	ns	3
Data to write time overlap	t_{DW}	10	—	10	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Write disable to output in low-Z	t_{OW}	3	—	3	—	ns	4
Write enable to output in high-Z	t_{WHZ}	—	7	—	7	ns	4

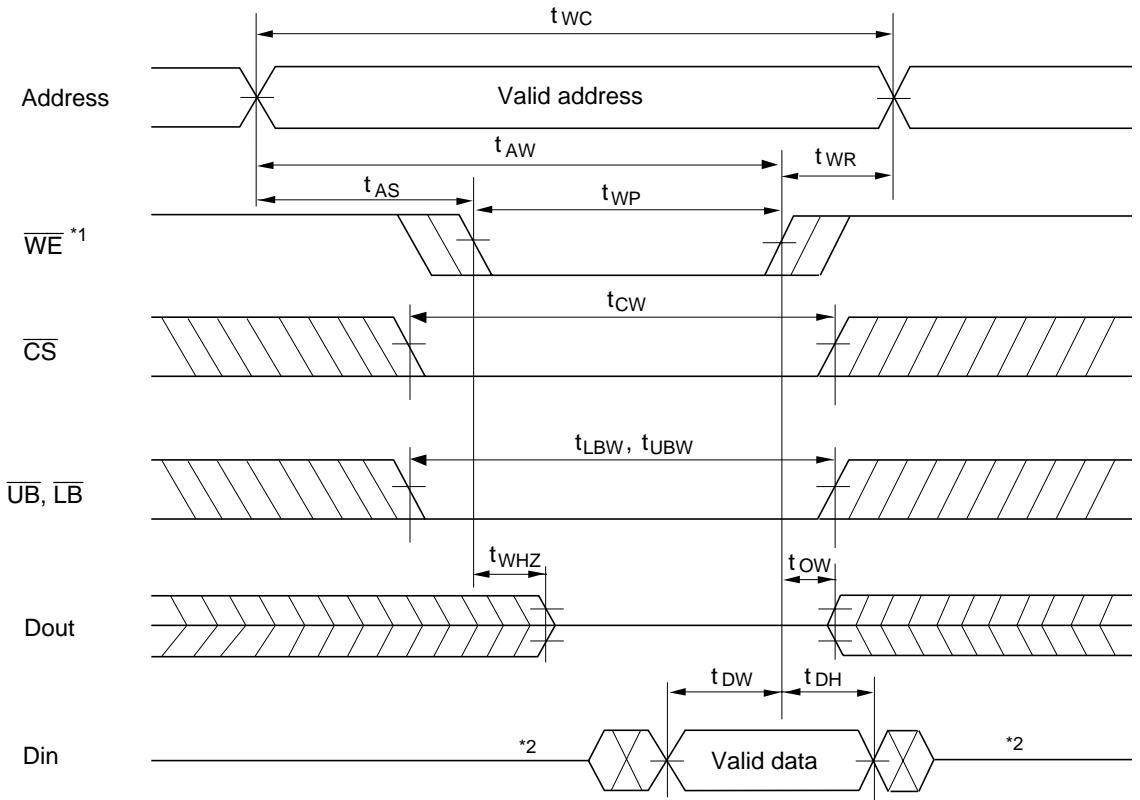
Notes: 1. A write occurs during the overlap of low \overline{CS} , low \overline{WE} and low \overline{LB} or low \overline{UB} .

2. t_{AS} is measured from the latest address transition to the latest of \overline{CS} , \overline{WE} , \overline{LB} or \overline{UB} going low.

3. t_{WR} is measured from the earliest of \overline{CS} , \overline{WE} , \overline{LB} or \overline{UB} going high to the first address transition.

4. Transition is measured ± 200 mV from high impedance state's voltage with Load (B). This parameter is sampled and not 100% tested.

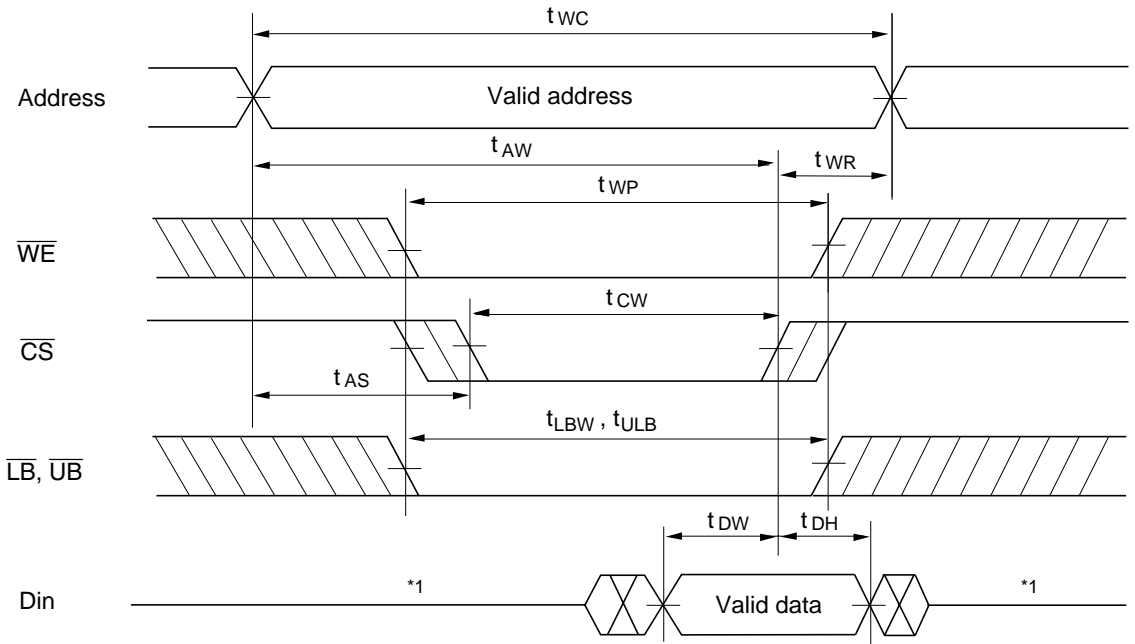
Write Timing Waveform (1) (\overline{WE} Controlled)



- Notes:
- \overline{WE} must be high during address transition except when the device is disabled with \overline{CS} , \overline{LB} or \overline{UB} .
 - If \overline{CS} , \overline{OE} , \overline{LB} and \overline{UB} are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.

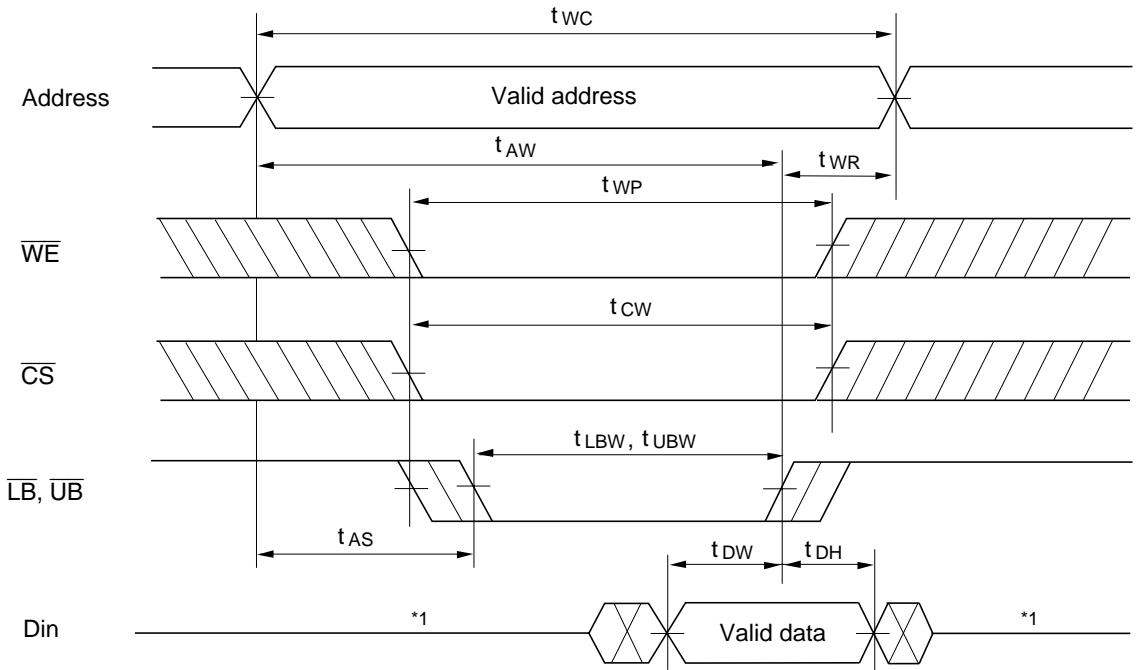
HM621664H/HM621864H Series

Write Timing Waveform (2) (\overline{CS} Controlled)



Note: 1. If the \overline{CS} or \overline{LB} or \overline{UB} low transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, output remains a high impedance state.

Write Timing Waveform (3) (\overline{LB} , \overline{UB} Controlled)



Note: 1. If the \overline{CS} or \overline{LB} or \overline{UB} low transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, output remains a high impedance state.

HM621664H/HM621864H Series

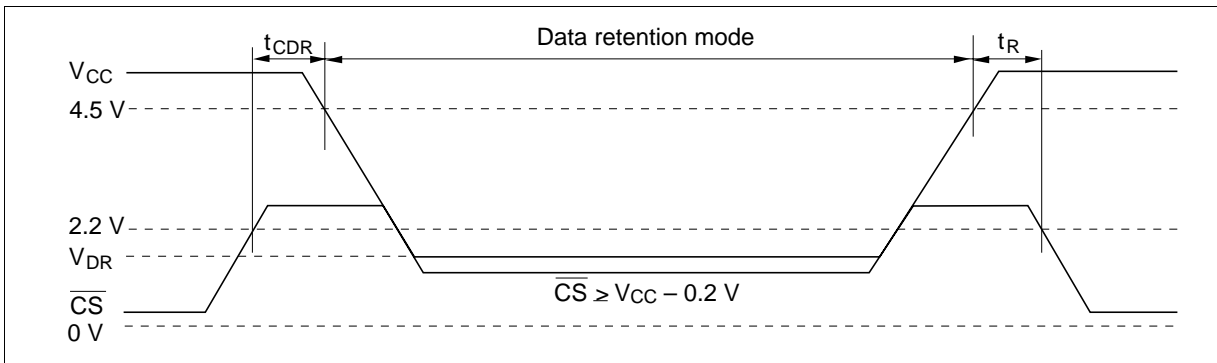
Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2 \text{ V}$, $V_{CC} \geq V_{in} \geq V_{CC} - 0.2 \text{ V}$ or $0 \text{ V} \leq V_{in} \leq 0.2 \text{ V}$
Data retention current	I_{CCDR}	—	2	80^{-1}	μA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

Note: 1. $V_{CC} = 3.0 \text{ V}$

Low V_{CC} Data Retention Timing Waveform



Package Dimension

HM621664HJP/HLJP, HM621864HJP/HLJP Series (CP-44D)

Unit: mm

